Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2654	257/778.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S2	361	S1 and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 10:22
S3	9764	(semiconductor or chip or die or ic or (integrated adj circuit)) and passivation and (via or terminal or electrode or lead or pad) and (interconnect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:42
S4	3996	"257"/\$6.ccls. and ((semiconductor or chip or die or ic or (integrated adj circuit)) and passivation and (via or terminal or electrode or lead or pad) and (interconnect))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:25
S5	2654	257/778.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 17:41
S6	361	S5 and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 10:25
S7∵.	· 3845	S4 not S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 10:26
S8	2551	S4 not S6	USPAT	OR	ON	2005/12/05 10:25

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S9	1895	S7 and (carrier or pcb or board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:38
S10	3996	"257"/\$6.ccls. and ((semiconductor or chip or die or ic or (integrated adj circuit)) and passivation and (via or terminal or electrode or lead or pad) and (interconnect))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	· OR	ON	2005/12/05 18:52
S11	2654	257/778.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 12:38
S12	361	S11 and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 12:38
S13	3845	S10 not S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:38
S14	1895	S13 and (carrier or pcb or board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 12:38
S15	898	S14 and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 13:28
S16	1154	(flip adj chip) and (passivation) and (interconnect or interlevel) and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:51

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S17	2091	257/784.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:52
S18	2048	S17 not S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 14:52
S19	239	S18 and passivation	US-PGPUB; USPAT; USOCR;	OR	ON	2005/12/05 16:16
			EPO; JPO; DERWENT; IBM_TDB			
S20	3112	(quad adj flat adj package)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:33
S22	298	((quad adj flat adj package) or qfp) and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:59
S23	37	S22 and (dicing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 17:06
S24	178	S22 and (wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2005/12/05 17:06
, ,			DERWENT; IBM_TDB			
S25	141	S24 not S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 17:06

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S26	1698	257/700.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 12:48
S27	1696 ·	S26 not S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 17:41
S28	148	S27 and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 18:44
S29	1548	S27 not S28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/05 18:44
S30	14213	"257"/\$6.ccls. and passivation and (via or terminal or electrode or lead or pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 18:52
S31	4112	S30 and (interconnect or intermetal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 18:54
S32	776	S31 and (flipchip or (flip adj chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:47
S33	14225	"257"/\$6.ccls. and passivation and (via or terminal or electrode or lead or pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:46

S3	4	1612	S33 and (flipchip or (flip adj chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/12/06 10:46
S3		4114	S33 and (interconnect or intermetal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:47
S3	6	776	S35 and (flipchip or (flip adj chip))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:47
S3	7	836	S34 not S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 10:49
S3	8	4917	(semiconductor or chip or die or ic or (integrated adj circuit)) and passivation and (via or terminal or electrode or lead or pad) and (interconnect) and (carrier or pcb or board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:44
S3	9	3388	(semiconductor or chip or die or ic or (integrated adj circuit)) and (passivation adj layer) and (via or terminal or electrode or lead or pad) and (interconnect) and (carrier or pcb or board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:43
S4	0	2642	S39 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:44
S4	1	1568	S39 and oxide	USPAT	OR	ON	2005/12/06 14:44
S4 :	2	1694	(multiple near5 (semiconductor or chip or die or ic or (integrated adj circuit))) and passivation and (via or terminal or electrode or lead or pad) and (interconnect) and (carrier or pcb or board or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 14:45

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S43	6082	(quad adj flat) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/26 18:11
S44	1526	(quad adj flat near3 lead) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/05 11:40
S45	2574	"257"/\$6.ccls. and (quad adj flat) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/26 18:11
S46	1550	(quad adj flat near3 lead) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/26 18:12
S47	2575	"257"/\$6.ccls. and (quad adj flat) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:40
S48	1551	(quad adj flat near3 lead) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:45
S49	1329	S47 not S48	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF.	2006/05/30 10:03
S50	4311	wafer near3 ceramic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/30 10:04

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S51	348	"257"/\$6.ccls. and (wafer near3 ceramic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/30 10:04
S52	1782	257/e23.02.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 13:49
S53	176	257/e23.031.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 12:48
S54	179	257/e23.034.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 12:48
S55		S53 S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S56	1781	S52 not S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S57	1931	(semiconductor or ic or chip or die or (integrated adj circuit) or (electronic adj device)) and (quad adj flat near3 (lead or no-lead)) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 13:51
S58 _.	1964	257/690.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07

S59	693	257/685.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S60	2612	S58 S59	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S61	2556	S60 not S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S62	1782	257/e23.02.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S63	2504	S61 not S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	OFF	2007/01/17 16:07
S64	176	257/e23.031.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:07
S65	2498	S63 not S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 16:08
S66	1338	S63 not S64	USPAT; USOCR	OR	OFF	2007/01/17 16:08
S67	1160	S63 not S64	US-PGPUB; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54

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S68	232	("257"/\$6.ccls. and (quad adj flat) or (qfn)) and @pd>"20070117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S69	183	((quad adj flat near3 lead) or (qfn)) and @pd>"20070117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:45
S70	190	((semiconductor or ic or chip or die or (integrated adj circuit) or (electronic adj device)) and (quad adj flat near3 (lead or no-lead)) or (qfn)) and @pd>"20070117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 13:51
S71	196	257/e23.031.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S72	184	257/e23.034.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S73	20	(S71 S72) and @pd>"20070117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S74	2119	(semiconductor or ic or chip or die or (integrated adj circuit) or (electronic adj device)) and (quad adj flat near3 (lead or no-lead)) or (qfn)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 13:54
S75	2044	257/690.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54

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S76	742	257/685.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S77	2738	S75 S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S78	2676	S77 not S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S79	1932	257/e23.02.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S80	2620	S78 not S79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S81	196	257/e23.031.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S82	41	(S80 not S81) and @pd>"20070117"	US-PGPUB; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:54
S83	1932	257/e23.02.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55

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S84	380	S71 S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S85	56	(S83 not S84) and	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S86	20	(S71 S72) and @pd>"20070117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 13:55
S87	366	S68 S69 S70 S73 S82 S85 S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 14:47
S88	2906	257/774.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/28 14:48
S89	1226	257/774.ccls. and ((si or silicon) near3 (wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/28 14:48
S90	217730	(semiconductor or ic or chip or (integrated adj circuit) or (electronic adj device) or die) and (carrier or interposer) and via	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/29 13:35
S91	18773	(semiconductor or ic or chip or (integrated adj circuit) or (electronic adj device) or die) SAME (carrier or interposer) same via	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/29 13:36

S92	3958	((semiconductor or ic or chip or (integrated adj circuit) or (electronic adj device) or die) SAME (carrier or interposer) same via) and (interconnect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/29 13:37
S93	1018	(semiconductor or ic or chip or (integrated adj circuit) or (electronic adj device) or die) SAME (carrier or interposer) same via same (interconnect)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/29 13:37